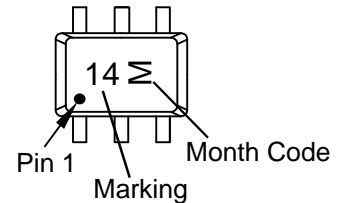
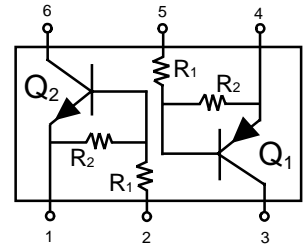
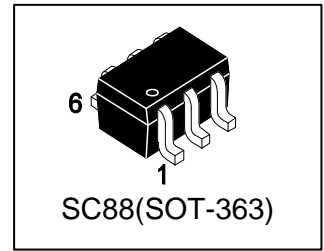


LMUN5314DW1T1G

S-LMUN5314DW1T1G

Dual Bias Resistor Transistors
NPN and PNP Silicon Surface Mount Transistors
with Monolithic Bias Resistor Network



1. FEATURES

- Simplifies circuit design
- Reduces board space.
- Reduces Component Count
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1(K)	R2(K)	Shipping
LMUN5314DW1T1G	14	10	47	3000/Tape&Reel
LMUN5314DW1T3G	14	10	47	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	50	V
Collector–Base Voltage	VCBO	50	V
Collector Current — Continuous	IC	100	mA

4. THERMAL CHARACTERISTICS

Parameter (One Junction Heated)	Symbol	Limits	Unit
Total Device Dissipation, (Note 1) @ TA = 25°C Derate above 25°C	PD	187 1.5	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	670	°C/W
Parameter (Both Junctions Heated)	Symbol	Limits	Unit
Total Device Dissipation, (Note 1) @ TA = 25°C Derate above 25°C	PD	250 2	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	493	°C/W
Thermal Resistance, Junction–to–Lead(Note 1)	RθJL	188	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

1. FR-4 @ Minimum Pad

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 2.0 mA, IB = 0)	VBR(CEO)	50	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA, IE = 0)	VBR(CBO)	50	-	-	V
Collector-Base Cutoff Current (VCB = 50 V, IE = 0)	ICBO	-	-	100	nA
Collector-Emitter Cutoff Current (VCE = 50 V, IB = 0)	ICEO	-	-	500	nA
Emitter-Base Cutoff Current (VEB = 6.0 V, IC = 0)	IEBO	-	-	0.2	mA

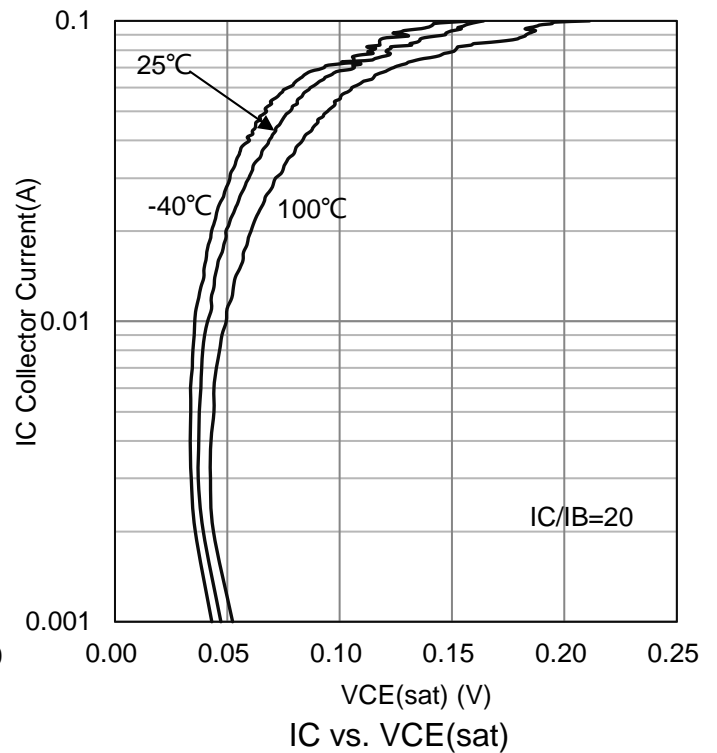
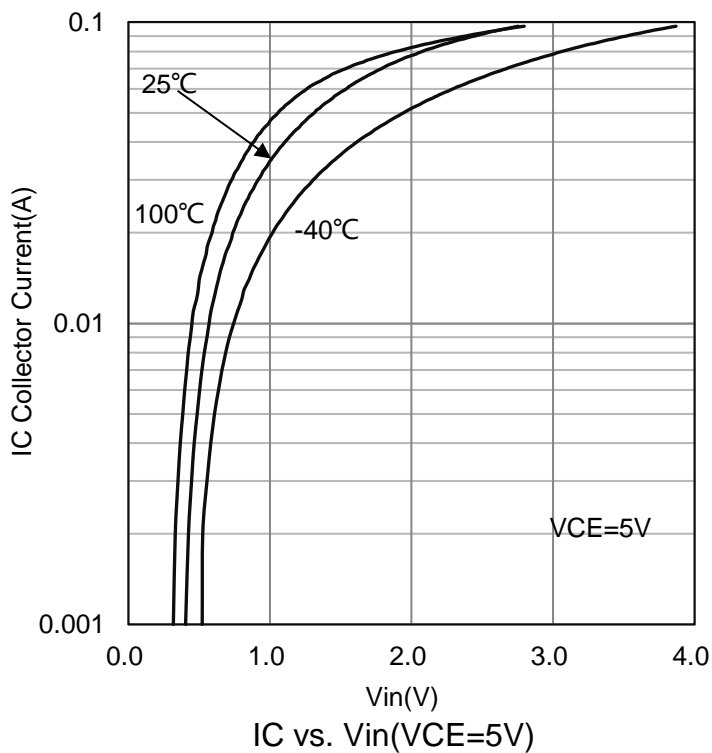
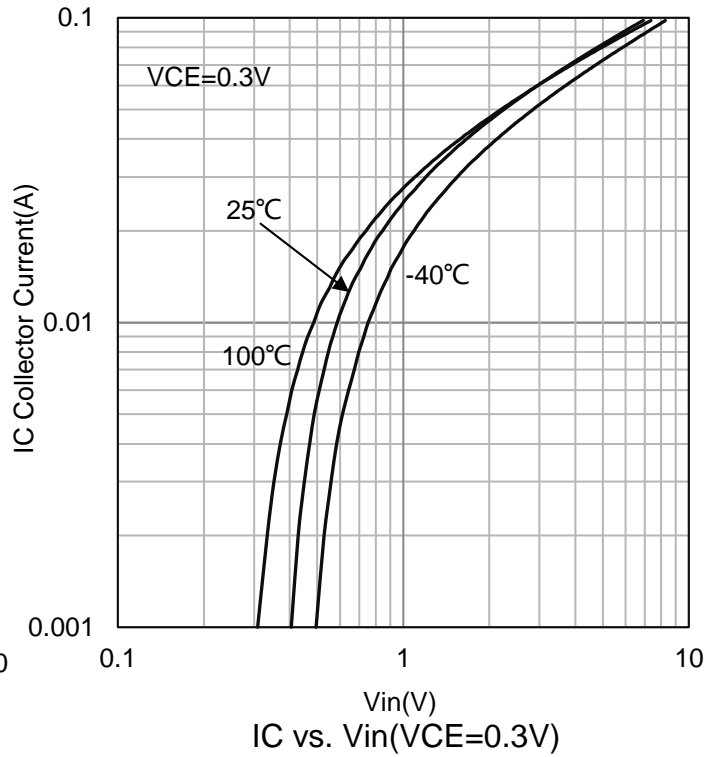
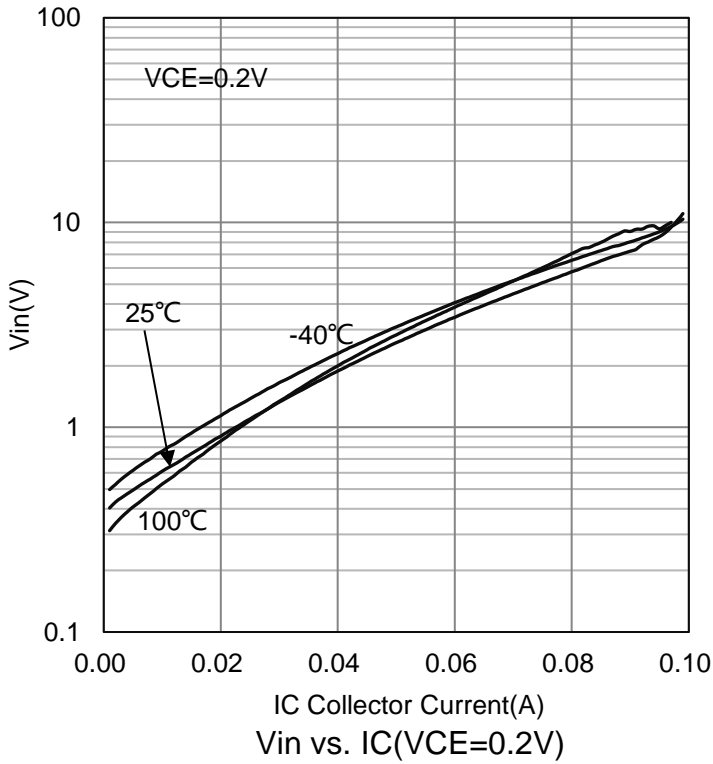
ON CHARACTERISTICS (Note 2.)

DC Current Gain (IC = 5.0 mA, VCE = 10 V)	HFE	80	140	-	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.3 mA)	VCE(sat)	-	-	0.25	V
Output Voltage (on) (VCC = 5.0 V, VB = 2.5 V, RL = 1.0KΩ)	VOL	-	-	0.2	V
Output Voltage (off) (VCC = 5.0 V, VB = 0.5 V, RL = 1.0KΩ)	VOH	4.9	-	-	V
Input Resistor	R1	7	10	13	KΩ
Resistor Ratio	R1/R2	0.17	0.21	0.25	

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

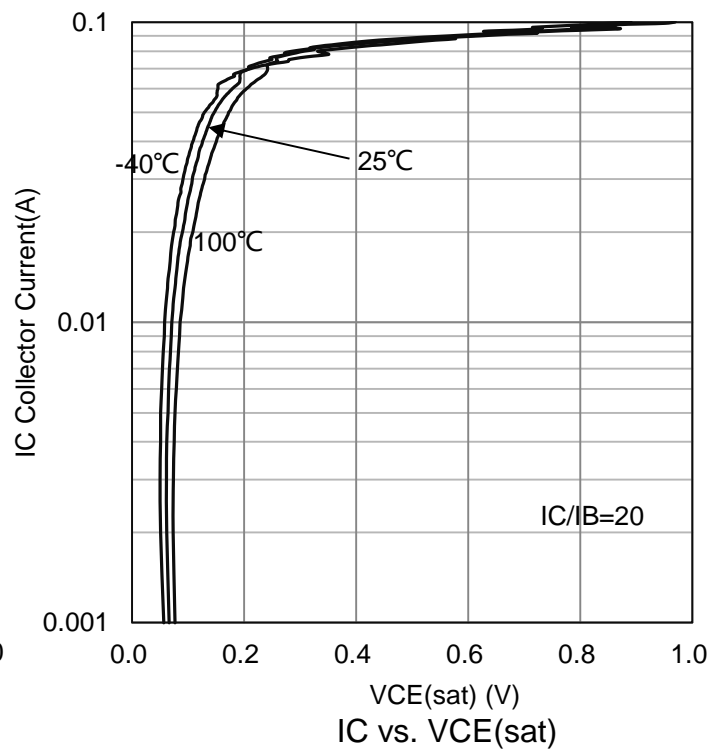
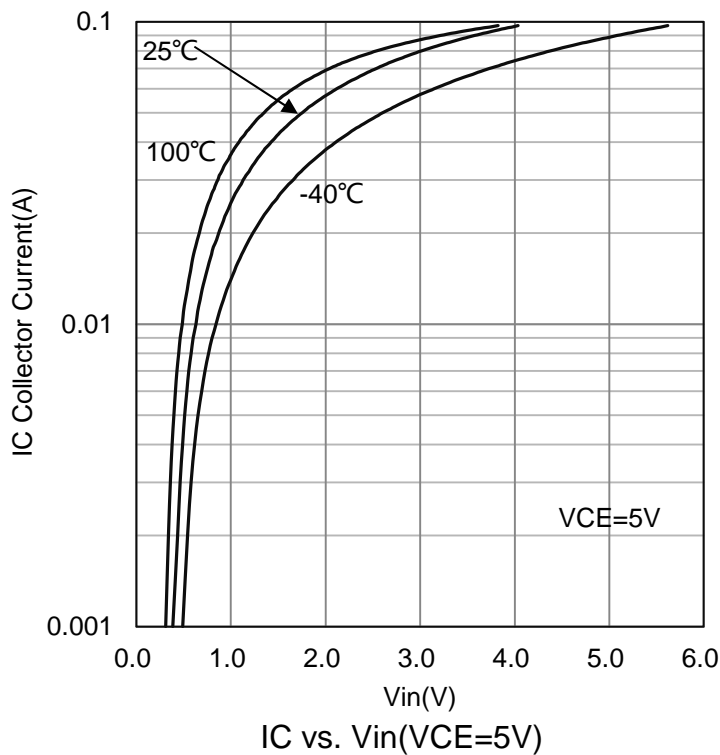
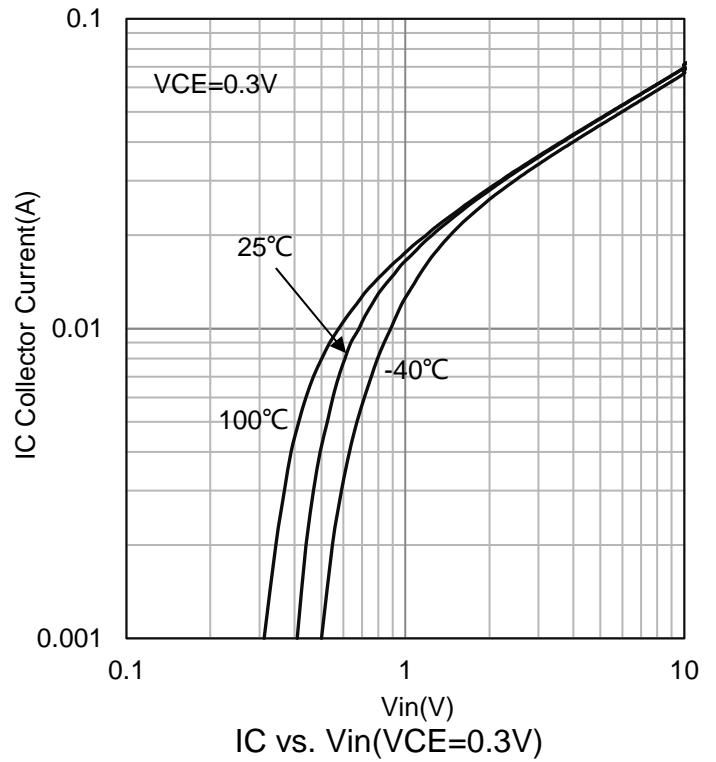
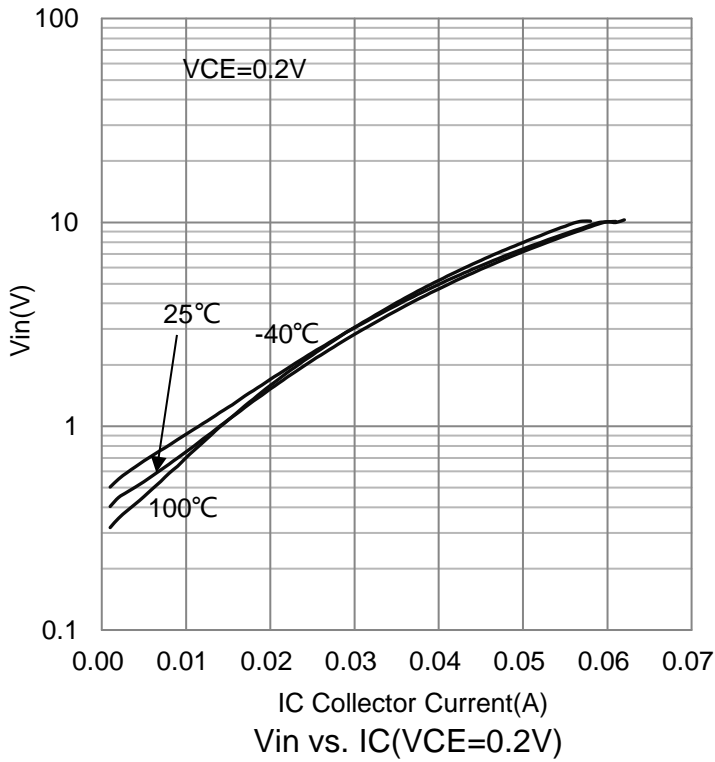
6. ELECTRICAL CHARACTERISTICS CURVES

NPN



6. ELECTRICAL CHARACTERISTICS CURVES(Con.)

PNP



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)